

# ZINC OXIDE

## for 1550 nm sensing applications

### INTRODUCTION

Zinc oxide (ZnO) can be used as a smart material in (among other things) electro-optical or piezo-electrical devices. Up to now LioniX has focused material research on the electro-optical properties of ZnO, for application in integrated optical (IO) circuits. An example of an IO circuit, which utilises the electro-optical properties of ZnO, is the integrated optical Mach-Zehnder Interferometer (IO-MZI).

LioniX has optimized ZnO deposition parameters to optimize optical performance wavelengths of 633, 850 and 1550 nm.

### ZINC OXIDE TECHNOLOGY

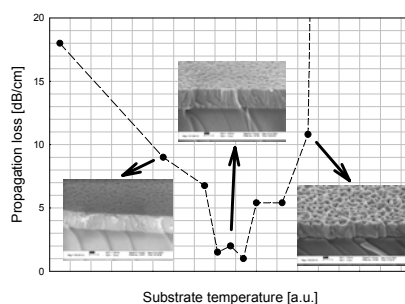
ZnO is deposited using a DC triode sputtering machine owned by LioniX, see photograph below.



The growth temperature and post-deposition annealing have a strong influence on the resulting optical losses (absorption per unit propagation length, dB/cm). The growth temperature has been optimized; see the graph below comparing various situations.

In the region where the absorption losses are minimal, post-deposition annealing is no longer required. The electro-optical coefficient of ZnO is not influenced significantly. This was checked using the Teng-Man technique.

**Figure 1 Propagation loss of ZnO.**



The magnitude of the electro-optic effect of ZnO is 1.4 pm/V. The structure of *as deposited* ZnO on top of amorphous SiO<sub>2</sub> or Si<sub>3</sub>N<sub>4</sub> is preferentially *c*-axis oriented polycrystalline. Therefore ZnO does not require poling for activation of the electro-optical or piezo-electrical properties. Other electro-optical crystals such as P(L)ZT or BaTiO<sub>3</sub> can be grown preferentially *c*-axis oriented only on top of special materials such as SrTiO<sub>3</sub> which are much more expensive and available only in small sizes. Electro-optical polymers always require poling after deposition, have adhesion problems, and do not allow temperatures above 150 °C in further processing.

Another convenient property of ZnO is that its refractive index is very close to that of LPCVD Si<sub>3</sub>N<sub>4</sub>, which allows fabrication of very high contrast IO waveguiding structures with a mix of Si<sub>3</sub>N<sub>4</sub> and ZnO as core layer material.

### REFERENCE

Heideman, R.G., Lambeck, P.V., SENSORS AND ACTUATORS B, VOL 61, 1999

Teng, C.C., Man, H.T., Appl.Phys.Lett., Vol.56, No.18,30 April 1990

### ACKNOWLEDGMENT

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### LIONI X MISSION STATEMENT

LioniX is a leading provider in development and small to high volume production of leveraging and innovative products based on microsystem technology and MEMS. Our core technologies are integrated optics and microfluidics.

### FROM WHOM WE WORK

Our customers operate in telecom, industrial process control, life sciences and spaces markets and include OEM's, multinationals, VC start-up companies as well as research institutions from around the world.

### OUR BUSINESS FORMULA

LioniX offers design for manufacturing and horizontal integration by partnering with MEMS/MST foundries and suppliers of complementary technologies. Cooperations are based on subcontracting, licensing of IP or joint ventures.

### TECHNOLOGY

#### IPR

LioniX has an IPR agreement on technology with the world-renowned MESA+ institute and is rapidly building up a firm IPR position in its core competences integrated optics and microfluidics.

#### Facilities

LioniX uses state-of-the-art facilities of MESA+ Institute, as well as private facilities for our core technologies.

Our processes are performed on 100 mm silicon, borosilicate, quartz and other substrates.

- CVD deposition
- PECVD silicon-oxynitrides
- LPCVD Silicon-rich-nitride
- LPCVD Silicon-nitride
- LPCVD polysilicon